

Room F (Sicily), 2F

Chair: Tatsuro Hiraki (NTT, inc.)

We1F

July 1 (Wed), 2026

III-V on Silicon Active Devices II & Electronic ICs

08:30-10:00

We1F-1 Invited 08:30-09:00

Ultra-Low Power SiGe ASIC for InP Mach Zehnder Modulator and CMOS Quenching-IC for SPAD for QKD Communication

Jung Han Choi

Fraunhofer Institute for Telecommunications, Heinrich Hertz Institute

We1F-2 09:00-09:15

Demonstration of Microdisk Modulator Driven by InP/Si Hybrid SIS Capacitor

Kyunghwan Kim, Jae-Hoon Han

Korea Institute of Science and Technology

We1F-3 09:15-09:30

Heterogeneously Integrated III-V/Si Semiconductor Optical Amplifier Switch

Jaeseong Jeon, Il-Sug Chung

Ulsan National Institute of Science and Technology

We1F-4 09:30-09:45

20 dB Gain Heterogeneous Integration Semiconductor Optical Amplifier on 220nm Silicon-on-Insulator Platform

Haibo Kuang, Guobiao Tang, Yu Zhang

Huazhong University of Science and Technology

We1F-5 09:45-10:00

Heterogeneously Integrated Vernier Laser with 45-nm Tuning Range

Sangmin Oh, Il-Sug Chung

Ulsan National Institute of Science and Technology